

At page 7, please replace paragraphs [022] and [023] with the following paragraphs:

M

Fig. 3a illustrates a cross-sectional view taken along line I-I' of Fig. 2b;

Fig. 3b illustrates a cross-sectional view taken along line II-II' of Fig. 2b;

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The changes made to paragraphs [022] and [023] are indicated by brackets for deletions and underlining for insertions.

Fig. 3a illustrates a cross-sectional view taken along line [A-A'] I-I' of Fig. 2b;

Fig. 3b illustrates a cross-sectional view taken along line [B-B'] II-II' of Fig. 2b;

At page 10, please replace paragraph [032] with the following paragraph:

A2  
Fig. 3a illustrates a cross-section view taken along the line I-I' of Fig. 2b, and Fig. 3b illustrates a cross-sectional view taken along the line II-II' of Fig. 2b. Referring to Figs. 3a and 3b together, in order to protect integrated circuits on the wafer from the difference of CTE between a passivation layer 12 such as SiN, SiON, etc. and a metal that is used in wiring and connection patterns, such as silver (Ag), copper (Cu), and from the mechanical damage, a first dielectric layer 60 is interposed therebetween. This first dielectric layer 60 serves as a stress buffer and improves the electrical signal response properties. The first dielectric layer 60 is preferably comprised of a polyimide material (dielectric constant: 2.8) with a thickness of about 2 microns to about 50 microns.

The changes made to paragraph [032] are indicated by brackets for deletions and underlining for insertions.

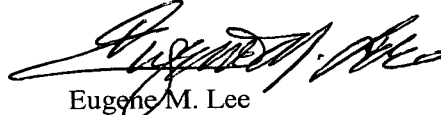
Fig. 3a illustrates a cross-section view taken along the line [A-A'] I-I' of Fig. 2b, and Fig. 3b [is] illustrates a cross-sectional view taken along the line [B-B'] II-II' of Fig. 2b. Referring to Figs. 3a and 3b together, in order to protect integrated circuits on the wafer from the difference of CTE between a passivation layer 12 such as SiN, SiON, etc. and a metal that is used in wiring and connection patterns, such as silver (Ag), copper (Cu), and from the mechanical damage, a first dielectric layer 60 is interposed therebetween. This first dielectric layer 60 serves as a stress buffer and improves the electrical signal response properties. The first dielectric layer 60 is preferably comprised of a polyimide material (dielectric constant: 2.8) with a thickness of about 2 microns to about 50 microns.

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The amendments made to the specification were necessary to correspond to the drawing corrections as requested by the Official Draftsman.

Receipt of the initial Office Action on the merits is awaited.

Respectfully submitted,  
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